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We claim:

1. A semiconductor wafer, comprising:

a plurality of pits in the semiconductor wafer, the pits being arranged in an information-providing pattern and being readable before, during and after completion of processing on the wafer.

- 2. The wafer according to claim 1, wherein the readability of the pits is provided by the pits having sufficient contrast with surrounding portions of the wafer.
- 3. The wafer according to claim 2, wherein the pits are arranged in a region of the wafer, wherein the contrast is provided by ion implant in the region.
- 4. The wafer according to claim 3, wherein the ion implant is carried out to a depth and the pits have a depth greater than the ion implant depth.
- 5. The wafer according to claim 2, wherein the pits are arranged in a region of the wafer, wherein the contrast is provided by the pits having a sufficient depth.
- bar code, a digital pattern, a binary pattern, or an alphanumeric pattern.
- 7. The wafer according to claim 6, wherein the digital pattern comprises long and short pits.
- 8. The wafer according to claim 1, wherein the plurality of pits comprise pits of a first shape and pits of a second shape.

9. The wafer according to claim 1, wherein the pits are on at least one surface of
the wafer selected from the group consisting of a front surface, a back surface, and a side
surface.

- 10. The wafer according to claim 1, wherein the pits are at least 2.5 um deep.
- 11. The wafer according to claim 1, wherein the pits are on a side surface of the wafer extending from a front surface of the wafer to a back surface of the wafer.
- 12. The wafer according to claim 11, wherein the pits on the side surface of the wafer are formed prior to slicing the wafer from a boule by providing diagonal lines in the boule to provide a unique pattern on each wafer sliced from the boule.
- 13. The wafer according to claim 1, wherein the pits are readable by a reader's eye.
- 14. The wafer according to claim 1, wherein the pits are readable with a laser reading device.
- 15. The wafer according to claim 1, further comprising a coating on the surface of the pits.
- 16. The wafer according to claim 1, wherein the pits have a width of at most about 1 mm and a depth of at most about 1 mm.
 - 17. The wafer according to claim 1, wherein a bottom surface of the pits is BU9 99 157

curved.

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- 18. The wafer according to claim 1, wherein at least one of the pits is perpendicular to a top surface and a bottom surface of the wafer.
- 19. The wafer according to claim 1, wherein at least one of the pits is angled with respect to a line perpendicular to a top surface and a bottom surface of the wafer.
- 20. The wafer according to claim 1, wherein at least one of the pits has curved sidewalls.
- 21. The wafer according to claim 1, wherein the pits have at least two different widths.
 - 22. The wafer according to claim 1, wherein the pits are machine-readable.
- 23. The wafer according to claim 8, wherein the pits are arranged in the back surface of the wafer.
- 24. The wafer according to claim 23, wherein groups of the pits have the shape of at least one of letters and numbers.
- 25. The wafer according to claim 24, wherein each group of pits has a width of about 2 mm and a height of about 5 mm.

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26. The wafer according to claim 24, wherein adjacent groups of pits are			
separated from each other by a distance of about 2 mm.			

- 27. The wafer according to claim 24, wherein each group of pits includes a machine-readable set of spaces for pits, each space comprising 2 columns each comprising 32 pits.
- 28. The wafer according to claim 1, wherein light striking spaces between the pits form interference fringes.
 - 29. The wafer according to claim 1, wherein light striking the pits is not reflected.
- 30. The wafer according to claim 1, wherein light striking the pits is reflected with a phase change.
- 31. The wafer according to claim 1, wherein the pits comprise at least one location pit for providing locational reference to a plurality of informational pits.
- 32. The wafer according to claim 31, wherein the location pit is arranged in a side edge of the wafer and the informational pits are located in a top surface or a bottom surface of the wafer.
- 33. The wafer according to claim 1, wherein the pits have the same widths and at least two different lengths.

- 34. The wafer according to claim 33, wherein the pits are arranged in at least one line.
- 35. The wafer according to claim 33, wherein adjacent pits in a line or in adjacent lines are separated by a distance of at least 5 Fm.
- 36. The wafer according to claim 15, wherein the coating is sapphire or silicon carbide.

1/2	\sum_{i}	37. A method of encoding information on a semiconductor wafer, comprising:
13/	2	converting the information into a digital form; and
	3	forming pits readable before, during and after completion of processing on the
	4	wafer corresponding to the digital form of the information in the semiconductor wafer.
	1	38. The method according to claim 37, wherein forming the pits comprises:
	2	forming a line of pits having two different lengths, the line of pits corresponding
	3	to the digital form of the information.
	1	39. The method according to claim 37, further comprising:
	2	forming a reference point, such that the pits are located a predetermined distance
	3	from the reference point.
	1	40. The method according to claim 37, further comprising:
	2	providing the pits with a detectable contrast with respect to surrounding portions
	3	of the wafer.
	1	41. The method according to claim 37, wherein the pits are formed prior to
14	2	cutting the wafer from a boule and forming the pits comprises:
	3	forming a first, curved groove in the boule;
	4	forming at least one linear groove in the boule; and
	5	slicing the boule into wafers.
	1	42. The method according to claim 37, further comprising:
2	2	coating the pits with a coating.

43. The method according to claim 37, further comprising:

reading the information represented by the pits.

invalidated.

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51. A system for encoding inf	formation on a semiconductor wafer and reading the
information, the system comprising:	

a plurality of pits formed on the semiconductor wafer in an information-providing pattern and being readable before, during and after completion of processing on the wafer; and

means for reading the information encoded by the pits.

- 52. The system according to claim 51, wherein the information reading means comprises at least one laser.
- 53. The system according to claim 51, wherein the information reading means comprises at least one interferometer.
- 54. The system according to claim 51, wherein the information reading means comprises at least one linear diode array.

